

# S-57GD S Series

Applications

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# AUTOMOTIVE, 150°C OPERATION, HIGH-WITHSTAND VOLTAGE, HIGH-SPEED, OMNIPOLAR DETECTION TYPE HALL EFFECT SWITCH IC

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Rev.1.3\_00

This IC, developed by CMOS technology, is a high-accuracy Hall effect switch IC that operates with high temperature and high-withstand voltage.

The output voltage level changes when this IC detects the intensity level of magnetic flux density. Using this IC with a magnet makes it possible to detect the open / close in various devices.

ABLIC Inc. offers a "magnetic simulation service" that provides the ideal combination of magnets and our Hall effect ICs for customer systems. Our magnetic simulation service will reduce prototype production, development period and development costs. In addition, it will contribute to optimization of parts to realize high cost performance. For more information regarding our magnetic simulation service, contact our sales representatives.

ABLIC Inc. offers FIT rate calculated based on actual customer usage conditions in order to support customer functional safety design.

For more information regarding our FIT rate calculation, contact our sales representatives.

# Caution This product can be used in vehicle equipment and in-vehicle equipment. Before using the product for these purposes, it is imperative to contact our sales representatives.

#### Features

- Uses a thin (t0.80 mm max.) TSOT-23-3S or ultra-thin (t0.50 mm max.) HSNT-6(2025) package, contributing to the enhancement of the designs of devices
- Contributes to accurate mechanism operation with high-accuracy magnetic characteristics (Refer to  **Magnetic** Characteristics" for details.)
- Suitable for devices which require high quality due to the production system of this IC which certifies automotive application quality
- Contributes to device safe design with a built-in reverse voltage protection circuit and output current limit circuit

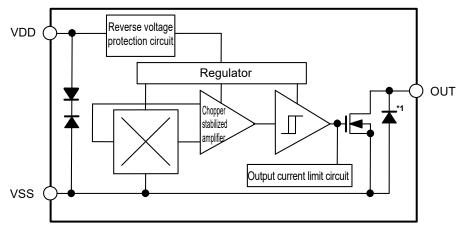
### Specifications

Pole detection:	Omnipolar detection	<ul> <li>Automobile equipment</li> </ul>
<ul> <li>Output logic<sup>*1</sup>:</li> </ul>	Active "L"	<ul> <li>Housing equipment</li> </ul>
	Active "H"	<ul> <li>Industrial equipment</li> </ul>
<ul> <li>Output form<sup>*1</sup>:</li> </ul>	Nch open-drain output	
	Nch driver + built-in pull-up resistor (1.2 k $\Omega$ typ.)	
<ul> <li>Magnetic sensitivity<sup>*1</sup>:</li> </ul>	B <sub>OP</sub> = 3.0 mT typ.	
	B <sub>OP</sub> = 6.0 mT typ.	Packages
	B <sub>OP</sub> = 10.0 mT typ.	
	B <sub>OP</sub> = 15.0 mT typ.	• TSOT-23-3S
<ul> <li>Chopping frequency:</li> </ul>	fc = 500 kHz typ.	• HSNT-6(2025)
<ul> <li>Output delay time:</li> </ul>	t <sub>D</sub> = 16.0 μs typ.	
<ul> <li>Power supply voltage range<sup>*2</sup>:</li> </ul>	V <sub>DD</sub> = 2.7 V to 26.0 V	
Built-in regulator		
Built-in reverse voltage protection	on circuit	

- Built-in output current limit circuit
- Operation temperature range:  $Ta = -40^{\circ}C \text{ to } +150^{\circ}C$
- Lead-free (Sn 100%), halogen-free
- AEC-Q100 qualified\*3
  - **\*1.** The option can be selected.
  - \*2.  $V_{DD}$  = 2.7 V to 5.5 V when output form is Nch driver + built-in pull-up resistor (1.2 k $\Omega$  typ.)
  - **\*3.** Contact our sales representatives for details.

# Block Diagrams

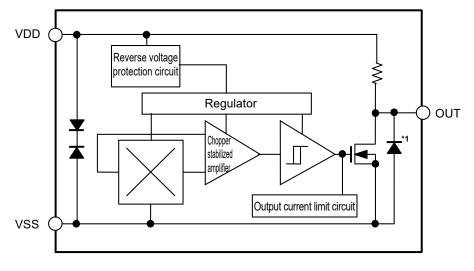
1. Nch open-drain output product



\*1. Parasitic diode



### 2. Nch driver + built-in pull-up resistor product



**\*1.** Parasitic diode

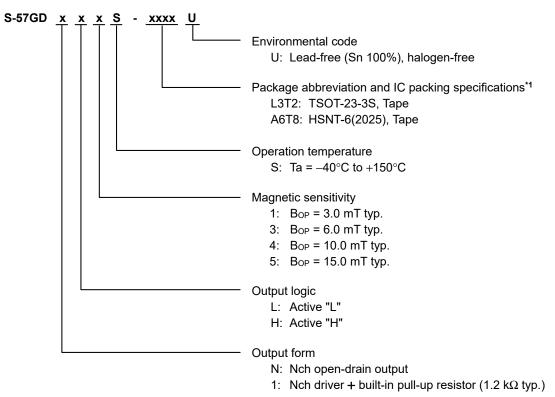
Figure 2

# ■ AEC-Q100 Qualified

This IC supports AEC-Q100 for operation temperature grade 0. Contact our sales representatives for details of AEC-Q100 reliability specification.

# Product Name Structure

1. Product name



\*1. Refer to the tape drawing.

#### 2. Packages

 Table 1
 Package Drawing Codes

Package Name	Dimension Tape Reel		Land	Stencil Opening	
TSOT-23-3S	MP003-E-P-SD	MP003-E-C-SD	D MP003-E-R-SD –		_
HSNT-6(2025)	PJ006-B-P-SD	PJ006-B-C-SD	PJ006-B-R-SD	PJ006-B-LM-SD	PJ006-B-LM-SD

#### 3. Product name list

#### 3.1 TSOT-23-3S

### Table 2

Product Name	Output Form	Power Supply Voltage Range	Output Logic	Magnetic Sensitivity (B <sub>OP</sub> )
S-57GDNL1S-L3T2U	Nch open-drain output	V <sub>DD</sub> = 2.7 V to 26.0 V		3.0 mT typ.
S-57GDNL3S-L3T2U	Nch open-drain output	V <sub>DD</sub> = 2.7 V to 26.0 V	Active "L"	6.0 mT typ.
S-57GDNL5S-L3T2U	Nch open-drain output	V <sub>DD</sub> = 2.7 V to 26.0 V	Active "L"	15.0 mT typ.

**Remark** Please contact our sales representatives for products other than the above.

#### 3.2 HSNT-6(2025)

#### Table 3

Product Name	Output Form	Power Supply Voltage Range	Output Logic	Magnetic Sensitivity (B <sub>OP</sub> )
S-57GDNL1S-A6T8U	Nch open-drain output	V <sub>DD</sub> = 2.7 V to 26.0 V		3.0 mT typ.
S-57GDNL3S-A6T8U	Nch open-drain output	V <sub>DD</sub> = 2.7 V to 26.0 V	Active "L"	6.0 mT typ.
S-57GDNL5S-A6T8U	Nch open-drain output	$V_{DD}$ = 2.7 V to 26.0 V	Active "L"	15.0 mT typ.

**Remark** Please contact our sales representatives for products other than the above.

# Pin Configurations

### 1. TSOT-23-3S

Top view



Table 4									
Pin No.	Symbol	Description							
1	VSS	GND pin							
2	VDD	Power supply pin							
3	OUT	Output pin							

Figure 3

#### 2. HSNT-6(2025)

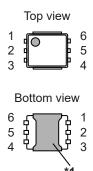


Figure 4

Table5									
Pin No.	Symbol	Description							
1	VDD	Power supply pin							
2	NC <sup>*2</sup>	No connection							
3	OUT	Output pin							
4	NC*2	No connection							
5	VSS	GND pin							
6	NC*2	No connection							

- \*1. Connect the heatsink of backside at shadowed area to the board, and set electric potential open or GND. However, do not use it as the function of electrode.
- \*2. The NC pin is electrically open. The NC pin can be connected to the VDD pin or the VSS pin.

# Absolute Maximum Ratings

Table 6

	Item	Symbol	Absolute Maximum Rating	Unit	
	Nch open-drain output product		$V_{\text{SS}}-28.0$ to $V_{\text{SS}}+28.0$	V	
Power supply voltage	Nch driver + built-in pull-up resistor V (1.2 k $\Omega$ typ.) product V		$V_{\text{SS}}-9.0$ to $V_{\text{SS}}+9.0$	V	
Power supply current		IDD	±10		
Output current		lout ±10			
	Nch open-drain output product		$V_{\rm SS}-0.3$ to $V_{\rm SS}+28.0$	V	
Output voltage	Nch driver + built-in pull-up resistor (1.2 k $\Omega$ typ.) product	Vout	$V_{\text{SS}} - 0.3$ to $V_{\text{DD}} + 0.3$	V	
Junction temperature		Tj	–40 to +170	°C	
Operation ambient temperature		Topr	-40 to +150	°C	
Storage temperature		T <sub>stg</sub>	-40 to +170	°C	

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

Table 7

# Thermal Resistance Value

Item	Symbol	Condition	Condition		Тур.	Max.	Unit
			Board A	-	225	_	°C/W
			Board B	-	190	-	°C/W
		TSOT-23-3S	Board C	I	_	-	°C/W
			Board D	1	_	_	°C/W
lumetice to evolviont the sum of vertication of *1			Board E	I	_	-	°C/W
Junction-to-ambient thermal resistance*1	θја		Board A	1	180	_	°C/W
			Board B	I	128	-	°C/W
		HSNT-6(2025)	Board C	I	43	-	°C/W
			Board D	I	44	-	°C/W
			Board E	-	36	_	°C/W

\*1. Test environment: compliance with JEDEC STANDARD JESD51-2A

**Remark** Refer to "**■ Power Dissipation**" and "**Test Board**" for details.

## Electrical Characteristics

#### 1. Nch open-drain output product

Table 8

(Ta =  $-40^{\circ}$ C to  $+150^{\circ}$ C, V<sub>DD</sub> = 2.7 V to 26.0 V, V<sub>SS</sub> = 0 V unless otherwise specified)

ltem	Symbol	Condition	Min.	Typ.*1	Max.	Unit	Test Circuit
Power supply voltage	V <sub>DD</sub>	_	2.7	12.0	26.0	V	-
Current consumption	I <sub>DD</sub>	_		4.0	4.5	mA	1
Current consumption during reverse connection	I <sub>DDREV</sub>	V <sub>DD</sub> = -26.0 V	-0.1	-	-	mA	1
Low level output voltage	Vol	Ιουτ = 5 mA, Vουτ = "L"	-	-	0.4	V	2
Leakage current	ILEAK	Vout = "H"		-	10	μA	3
Output limit current	Іом	V <sub>OUT</sub> = 12.0 V	11	I	35	mA	3
Output delay time*2	t⊳	_	Ι	16	32	μs	-
Chopping frequency*2	fc	_	250	500	-	kHz	-
Start up time*2	t <sub>PON</sub>	_		25	40	μs	4
Output rise time*2	t <sub>R</sub>	C = 20 pF, R = 820 Ω	_	_	1.0	μs	5
Output fall time*2	t⊧	C = 20 pF, R = 820 Ω	_	_	1.0	μs	5

\*1. Typ. value when Ta =  $+25^{\circ}$ C, V<sub>DD</sub> = 12.0 V.

\*2. This item is guaranteed by design.

#### 2. Nch driver + built-in pull-up resistor (1.2 k $\Omega$ typ.) product

#### Table 9

 $(Ta = -40^{\circ}C \text{ to } +150^{\circ}C, V_{DD} = 2.7 \text{ V to } 5.5 \text{ V}, V_{SS} = 0 \text{ V unless otherwise specified})$ 

ltem	Symbol	Condition	Min.	Typ.*1	Max.	Unit	Test Circuit
Power supply voltage	V <sub>DD</sub>	_	2.7	5.0	5.5	V	-
Current consumption	IDD	V <sub>OUT</sub> = "H"	_	4.0	4.5	mA	1
Low level output voltage	Vol	Ιουτ = 0 mA, Vουτ = "L"	-	_	0.4	V	2
High level output voltage	Vон	Ιουτ = 0 mA, Vουτ = "H"	$V_{\text{DD}} \times 0.9$	-	-	V	2
Output limit current	I <sub>ОМ</sub>	$V_{DD} = V_{OUT} = 5.0 V$	11	-	35	mA	3
Output delay time*2	tD	_	_	16	32	μs	-
Chopping frequency*2	f <sub>C</sub>	_	250	500	-	kHz	-
Start up time*2	t <sub>PON</sub>	—	_	25	40	μs	4
Output rise time*2	t <sub>R</sub>	C = 20 pF	_	_	1.0	μs	5
Output fall time*2	t <sub>F</sub>	C = 20 pF	_	_	1.0	μs	5
Pull-up resistor	RL	_	0.9	1.2	1.5	kΩ	_

**\*1.** Typ. value when Ta =  $+25^{\circ}$ C, V<sub>DD</sub> = 5.0 V.

\*2. This item is guaranteed by design.

Caution Due to limitation of the power dissipation, these values may not be satisfied. Attention should be paid to the power dissipation when using in high temperature operation environments.

# AUTOMOTIVE, 150°C OPERATION, HIGH-WITHSTAND VOLTAGE, HIGH-SPEED, OMNIPOLAR DETECTION TYPE HALL EFFECT SWITCH IC S-57GD S Series Rev. 1.3\_00

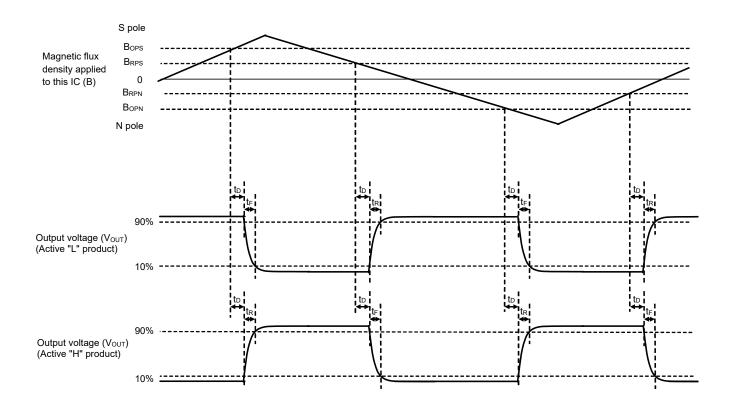


Figure 5 Operation Timing

### Magnetic Characteristics

#### 1. TSOT-23-3S

- 1. 1 Product with  $B_{OP} = 3.0 \text{ mT typ.}$ 
  - 1. 1. 1 Ta = +25°C

Table 10

(V <sub>DD</sub> = 5.0 V, V <sub>SS</sub> = 0 V unless otherwise specified								
Item		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Operation point*1	S pole	Bops	-	2.0	3.0	4.3	mT	4
	N pole	BOPN	-	-4.3	-3.0	-2.0	mT	4
Deleges reint*2	S pole	BRPS	_	1.2	2.2	3.2	mT	4
Release point*2	N pole	BRPN	_	-3.2	-2.2	-1.2	mT	4
Hysteresis width*3	S pole	BHYSS	BHYSS = BOPS – BRPS	_	0.8	_	mT	4
	N pole	BHYSN	BHYSN =  BOPN - BRPN	_	0.8	_	mT	4

#### 1. 1. 2 Ta = -40°C to +150°C\*4

			(V <sub>DD</sub> =	2.7 V to 26	6.0 V, Vss :	= 0 V unles	ss otherv	vise specified)
Item		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Operation point*1	S pole	BOPS	-	1.5	3.0	6.0	mT	4
	N pole	BOPN	-	-6.0	-3.0	-1.5	mT	4
Release point* <sup>2</sup>	S pole	BRPS	-	0.5	2.2	4.5	mT	4
Release point -	N pole	B <sub>RPN</sub>	-	-4.5	-2.2	-0.5	mT	4
Hysteresis width*3	S pole	BHYSS	BHYSS = BOPS - BRPS	-	0.8	-	mT	4
	N pole	B <sub>HYSN</sub>	BHYSN =  BOPN - BRPN	-	0.8	-	mT	4

#### Table 11

#### 1. 2 Product with $B_{OP} = 6.0 \text{ mT}$ typ.

#### 1. 2. 1 Ta = +25°C

Table 12

				(V <sub>DD</sub> = :	5.0 V, V <sub>SS</sub> :	= 0 V unles	ss otherv	vise specified)
Item		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Operation point <sup>*1</sup>	S pole	BOPS	-	4.0	6.0	8.0	mT	4
	N pole	BOPN	-	-8.0	-6.0	-4.0	mT	4
Dologoo point*2	S pole	B <sub>RPS</sub>	-	3.0	4.5	6.0	mT	4
Release point*2	N pole	B <sub>RPN</sub>	-	-6.0	-4.5	-3.0	mT	4
Hysteresis width <sup>3</sup>	S pole	B <sub>HYSS</sub>	B <sub>HYSS</sub> = B <sub>OPS</sub> – B <sub>RPS</sub>	-	1.5	_	mT	4
	N pole	B <sub>HYSN</sub>	BHYSN =  BOPN - BRPN	_	1.5	_	mT	4

#### 1. 2. 2 Ta = -40°C to +150°C\*4

Table 13

	$(V_{DD} = 2.7 \text{ V to } 26.0 \text{ V}, V_{SS} = 0 \text{ V unless otherwise specified})$									
Item		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit		
Operation point*1	S pole	BOPS	-	3.0	6.0	9.0	mT	4		
	N pole	BOPN	-	-9.0	-6.0	-3.0	mT	4		
Release point*2	S pole	B <sub>RPS</sub>	-	2.0	4.5	7.0	mT	4		
Release point -	N pole	BRPN	-	-7.0	-4.5	-2.0	mT	4		
Hysteresis width*3	S pole	B <sub>HYSS</sub>	B <sub>HYSS</sub> = B <sub>OPS</sub> – B <sub>RPS</sub>	_	1.5		mT	4		
	N pole	BHYSN	B <sub>HYSN</sub> =  B <sub>OPN</sub> - B <sub>RPN</sub>	_	1.5	_	mT	4		

#### AUTOMOTIVE, 150°C OPERATION, HIGH-WITHSTAND VOLTAGE, HIGH-SPEED, OMNIPOLAR DETECTION TYPE HALL EFFECT SWITCH IC S-57GD S Series Rev.1.3\_00

#### 1. 3 Product with $B_{OP} = 10.0 \text{ mT}$ typ.

#### 1. 3. 1 Ta = +25°C

#### Table 14

				(V <sub>DD</sub> = 5	5.0 V, Vss :	= 0 V unles	ss otherv	vise specified)
Item		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Operation point*1	S pole	Bops	_	7.2	10.0	12.6	mT	4
	N pole	BOPN	-	-12.6	-10.0	-7.2	mT	4
Deleges reint*2	S pole	B <sub>RPS</sub>	_	5.2	7.5	9.8	mT	4
Release point*2	N pole	BRPN	-	-9.8	-7.5	-5.2	mT	4
Hysteresis width*3	S pole	BHYSS	BHYSS = BOPS – BRPS	_	2.5	1	mT	4
	N pole	BHYSN	BHYSN = BOPN - BRPN	-	2.5	_	mT	4

#### 1. 3. 2 Ta = -40°C to +150°C\*4

#### Table 15

$(V_{DD} = 2.7 \text{ V to } 26.0 \text{ V}, \text{ V}_{SS} = 0 \text{ V unless otherwise specified})$								
Item		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Operation point <sup>*1</sup>	S pole	BOPS	-	5.6	10.0	13.8	mT	4
	N pole	BOPN	-	-13.8	-10.0	-5.6	mT	4
Dologoo point*2	S pole	BRPS	-	4.0	7.5	10.8	mT	4
Release point*2	N pole	BRPN	-	-10.8	-7.5	-4.0	mT	4
Hysteresis width <sup>*3</sup>	S pole	BHYSS	BHYSS = BOPS - BRPS	_	2.5	-	mT	4
	N pole	BHYSN	BHYSN =  BOPN - BRPN	-	2.5	-	mT	4

#### 1.4 Product with $B_{OP} = 15.0 \text{ mT typ.}$

#### 1. 4. 1 Ta = +25°C

Table 16

				(V <sub>DD</sub> =	5.0 V, Vss	= 0 V unles	ss otherv	vise specified)
Item		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Operation point*1	S pole	BOPS	_	11.2	15.0	19.2	mT	4
	N pole	BOPN	-	-19.2	-15.0	-11.2	mT	4
Delegge paint*2	S pole	BRPS	-	8.4	12.0	15.0	mT	4
Release point*2	N pole	B <sub>RPN</sub>	-	-15.0	-12.0	-8.4	mT	4
Hysteresis width*3	S pole	BHYSS	BHYSS = BOPS - BRPS	_	3.0	_	mT	4
	N pole	B <sub>HYSN</sub>	BHYSN =  BOPN - BRPN	-	3.0	-	mT	4

#### 1. 4. 2 Ta = -40°C to +150°C\*4

Table 17

			(V <sub>DD</sub> =	2.7 V to 2	6.0 V, V <sub>SS</sub> :	= 0 V unles	ss otherv	vise specified)
Item		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Operation point <sup>1</sup>	S pole	BOPS	_	8.8	15.0	21.4	mT	4
	N pole	BOPN	-	-21.4	-15.0	-8.8	mT	4
Release point*2	S pole	B <sub>RPS</sub>	-	6.8	12.0	16.8	mT	4
Release point -	N pole	B <sub>RPN</sub>	-	-16.8	-12.0	-6.8	mT	4
Hysteresis width <sup>*3</sup>	S pole	B <sub>HYSS</sub>	B <sub>HYSS</sub> = B <sub>OPS</sub> – B <sub>RPS</sub>	-	3.0	-	mT	4
	N pole	B <sub>HYSN</sub>	BHYSN =  BOPN - BRPN	-	3.0	-	mT	4

#### 2. HSNT-6(2025)

#### 2. 1 Product with $B_{OP} = 3.0 \text{ mT typ.}$

#### 2. 1. 1 Ta = +25°C

#### Table 18

				(V <sub>DD</sub> = 5	5.0 V, Vss :	= 0 V unles	s otherv	vise specified)
Item		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Operation point*1	S pole	BOPS	-	1.7	3.0	4.7	mT	4
	N pole	BOPN	-	-4.7	-3.0	-1.7	mT	4
Release point*2	S pole	BRPS	-	0.7	2.2	3.6	mT	4
Release point -	N pole	Brpn	-	-3.6	-2.2	-0.7	mT	4
Hysteresis width*3	S pole	BHYSS	BHYSS = BOPS - BRPS	_	0.8	_	mT	4
	N pole	BHYSN	BHYSN =  BOPN - BRPN	_	0.8	_	mT	4

#### 2. 1. 2 Ta = $-40^{\circ}$ C to $+150^{\circ}$ C<sup>\*4</sup>

Table 19 (V<sub>DD</sub> = 2.7 V to 26.0 V, V<sub>SS</sub> = 0 V unless otherwise specified) Symbol Condition Max. Unit Test Circuit Item Min. Тур. BOPS S pole 1.0 3.0 6.2 mΤ 4 \_ Operation point\*1 4 N pole Bopn \_ -6.2 -3.0 -1.0 mΤ Brps 2.2 5.0 4 S pole \_ 0.2 mΤ Release point\*2 N pole Brpn -5.0 -2.2 mΤ 4 -0.2 S pole BHYSS BHYSS = BOPS - BRPS 0.8 mΤ 4 — — Hysteresis width\*3 BHYSN = |BOPN - BRPN| N pole BHYSN \_ 8.0 \_ mT 4

### 2. 2 Product with $B_{OP} = 6.0 \text{ mT typ.}$

#### 2. 2. 1 Ta = +25°C

Table 20

				(V <sub>DD</sub> = 3	5.0 V, Vss	= 0 V unles	ss otherv	vise specified)
ltem		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Operation point*1	S pole	BOPS	-	3.7	6.0	8.3	mT	4
	N pole	BOPN	-	-8.3	-6.0	-3.7	mT	4
Delegge paint*2	S pole	BRPS	-	2.5	4.5	6.5	mT	4
Release point*2	N pole	B <sub>RPN</sub>	-	-6.5	-4.5	-2.5	mT	4
Hysteresis width*3	S pole	BHYSS	BHYSS = BOPS - BRPS	-	1.5	-	mT	4
	N pole	B <sub>HYSN</sub>	BHYSN =  BOPN - BRPN	_	1.5	_	mT	4

#### 2. 2. 2 Ta = $-40^{\circ}$ C to $+150^{\circ}$ C<sup>\*4</sup>

			(V <sub>DD</sub> =	2.7 V to 2	6.0 V, V <sub>SS</sub>	= 0 V unles	ss otherv	vise specified)
Item		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Operation point*1	S pole	BOPS	-	2.9	6.0	9.1	mT	4
	N pole	BOPN	_	-9.1	-6.0	-2.9	mT	4
Dologoo point*2	S pole	B <sub>RPS</sub>	-	1.7	4.5	7.3	mT	4
Release point* <sup>2</sup>	N pole	B <sub>RPN</sub>	-	-7.3	-4.5	-1.7	mT	4
Hysteresis width*3	S pole	B <sub>HYSS</sub>	B <sub>HYSS</sub> = B <sub>OPS</sub> – B <sub>RPS</sub>	-	1.5	-	mT	4
	N pole	B <sub>HYSN</sub>	BHYSN =  BOPN - BRPN	-	1.5	-	mT	4

Table 21

#### AUTOMOTIVE, 150°C OPERATION, HIGH-WITHSTAND VOLTAGE, HIGH-SPEED, OMNIPOLAR DETECTION TYPE HALL EFFECT SWITCH IC S-57GD S Series Rev.1.3\_00

#### 2. 3 Product with $B_{OP} = 10.0 \text{ mT typ.}$

#### 2. 3. 1 Ta = +25°C

#### Table 22

				(V <sub>DD</sub> = 5	5.0 V, Vss :	= 0 V unles	ss otherv	vise specified)
Item		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Operation point*1	S pole	BOPS	_	7.4	10.0	13.1	mT	4
	N pole	BOPN	-	-13.1	-10.0	-7.4	mT	4
Release point*2	S pole	BRPS	-	5.1	7.5	10.1	mT	4
Release point -	N pole	BRPN	-	-10.1	-7.5	-5.1	mT	4
Hysteresis width*3	S pole	BHYSS	BHYSS = BOPS - BRPS	_	2.5	-	mT	4
	N pole	BHYSN	BHYSN =  BOPN - BRPN	_	2.5	-	mT	4

#### 2. 3. 2 Ta = -40°C to +150°C\*4

Table 23(VDD = 2.7 V to 26.0 V, VSS = 0 V unless otherwise specified)										
Item Symbol Condition Min. Typ. Max. Unit Test Circuit										
Operation point <sup>*1</sup>	S pole	Bops	-	3.8	10.0	16.1	mT	4		
Operation point ·	N pole	BOPN	_	-16.1	-10.0	-3.8	mT	4		
Deleges reint*2	S pole	B <sub>RPS</sub>	_	2.7	7.5	12.5	mT	4		
Release point*2	N pole	BRPN	_	-12.5	-7.5	-2.7	mT	4		
Hysteresis width*3	S pole	BHYSS	BHYSS = BOPS - BRPS	_	2.5	Ι	mT	4		
	N pole	BHYSN	B <sub>HYSN</sub> =  B <sub>OPN</sub> - B <sub>RPN</sub>	_	2.5	-	mT	4		

#### 2. 4 Product with $B_{OP} = 15.0 \text{ mT typ.}$

#### 2. 4. 1 Ta = +25°C

Table 24

			14010 21	$(V_{PP} - )$			a othor	vise specified)
ltem		Symbol	Condition	Min.	<u></u>	Max.	Unit	Test Circuit
Operation point*1	S pole	Bops	-	10.6	15.0	19.9	mT	4
	N pole	BOPN	_	-19.9	-15.0	-10.6	mT	4
Delegge neint*2	S pole	Brps	_	8.1	12.0	15.8	mT	4
Release point*2	N pole	B <sub>RPN</sub>	-	-15.8	-12.0	-8.1	mT	4
Hysteresis width*3	S pole	BHYSS	BHYSS = BOPS - BRPS	_	3.0	1	mT	4
	N pole	BHYSN	BHYSN =  BOPN - BRPN	_	3.0	-	mT	4

### 2. 4. 2 Ta = -40°C to +150°C\*4

Table 25

			(V <sub>DD</sub> =	2.7 V to 2	6.0 V, V <sub>SS</sub>	= 0 V unles	ss otherv	vise specified)
Item		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Operation point*1	S pole	B <sub>OPS</sub>	_	6.4	15.0	23.5	mT	4
	N pole	BOPN	-	-23.5	-15.0	-6.4	mT	4
Release point*2	S pole	B <sub>RPS</sub>	-	4.6	12.0	19.6	mT	4
	N pole	B <sub>RPN</sub>	-	-19.6	-12.0	-4.6	mT	4
Hysteresis width*3	S pole	B <sub>HYSS</sub>	B <sub>HYSS</sub> = B <sub>OPS</sub> – B <sub>RPS</sub>	_	3.0	_	mT	4
	N pole	BHYSN	BHYSN =  BOPN - BRPN	_	3.0	_	mT	4

#### \*1. BOPN, BOPS: Operation points

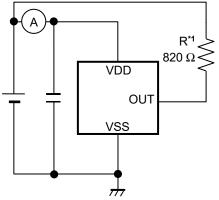
B<sub>OPN</sub> and B<sub>OPS</sub> are the values of magnetic flux density when the output voltage (V<sub>OUT</sub>) changes after the magnetic flux density applied to this IC by the magnet (N pole or S pole) is increased (by moving the magnet closer). Even when the magnetic flux density exceeds B<sub>OPN</sub> or B<sub>OPS</sub>, V<sub>OUT</sub> retains the status.

- \*2. B<sub>RPN</sub>, B<sub>RPS</sub>: Release points
   B<sub>RPN</sub> and B<sub>RPS</sub> are the values of magnetic flux density when the output voltage (V<sub>OUT</sub>) changes after the magnetic flux density applied to this IC by the magnet (N pole or S pole) is decreased (the magnet is moved further away). Even when the magnetic flux density falls below B<sub>RPN</sub> or B<sub>RPS</sub>, V<sub>OUT</sub> retains the status.
- \*3. B<sub>HYSN</sub>, B<sub>HYSS</sub>: Hysteresis widths B<sub>HYSN</sub> and B<sub>HYSS</sub> are the difference between B<sub>OPN</sub> and B<sub>RPN</sub>, and B<sub>OPS</sub> and B<sub>RPS</sub>, respectively.
- **\*4.** This item is guaranteed by design.

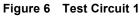
# Caution Due to limitation of the power dissipation, these values may not be satisfied. Attention should be paid to the power dissipation when using in high temperature operation environments.

**Remark** The unit of magnetic density mT can be converted by using the formula 1 mT = 10 Gauss.

# Test Circuits



\*1. Resistor (R) is unnecessary for Nch driver + built-in pull-up resistor product.



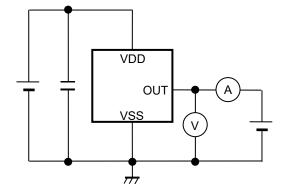
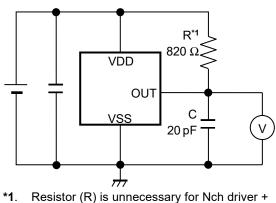
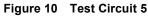
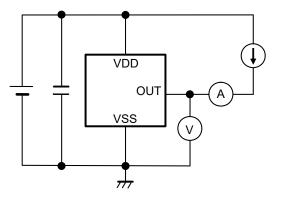


Figure 8 Test Circuit 3

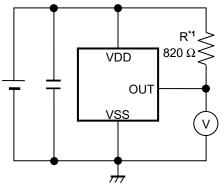


 Resistor (R) is unnecessary for Nch driver built-in pull-up resistor product.





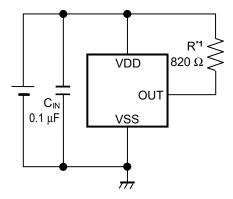




\*1. Resistor (R) is unnecessary for Nch driver + built-in pull-up resistor product.

#### Figure 9 Test Circuit 4

# Standard Circuit



\*1. Resistor (R) is unnecessary for Nch driver + built-in pull-up resistor product.

#### Figure 11

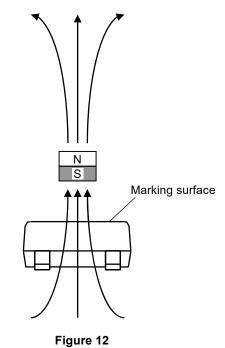
Caution The above connection diagram and constants will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constants.

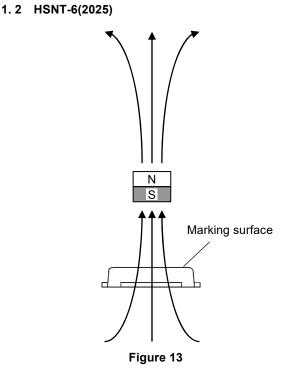
# Operation

#### 1. Direction of applied magnetic flux

This IC detects the magnetic flux density which is perpendicular to the package marking surface. A magnetic field is defined as positive when marking side of the package is the S pole, and negative when it is the N pole. Figure 12 and Figure 13 show polarity in a magnetic field and direction in which magnetic flux is being applied.

#### 1.1 TSOT-23-3S





#### 2. Position of Hall sensor

Figure 14 and Figure 15 show the position of Hall sensor.

The center of this Hall sensor is located in the area indicated by a circle, which is in the center of a package as described below.

The following also shows the distance (typ. value) between the marking surface and the chip surface of a package.

#### 2.1 TSOT-23-3S

#### 2.2 HSNT-6(2025)

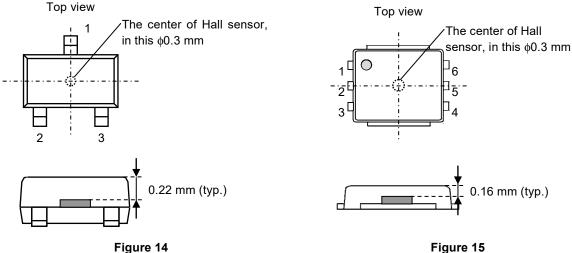


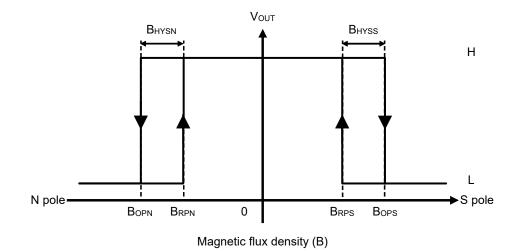
Figure 15

#### 3. Basic operation

This IC changes the output voltage ( $V_{OUT}$ ) according to the level of the magnetic flux density (N pole or S pole) applied by a magnet.

#### 3.1 Active "L" product

When the magnetic flux density perpendicular to the marking surface exceeds the operation point ( $B_{OPN}$  or  $B_{OPS}$ ) after the S pole or N pole of a magnet is moved closer to the marking surface of this IC,  $V_{OUT}$  changes from "H" to "L". When the S pole or N pole of a magnet is moved further away from the marking surface of this IC and the magnetic flux density is lower than the release point ( $B_{RPN}$  or  $B_{RPS}$ ),  $V_{OUT}$  changes from "L" to "H". **Figure 16** shows the relationship between the magnetic flux density and  $V_{OUT}$ .





#### 3. 2 Active "H" product

When the magnetic flux density perpendicular to the marking surface exceeds the operation point (B<sub>OPN</sub> or B<sub>OPS</sub>) after the S pole or N pole of a magnet is moved closer to the marking surface of this IC, V<sub>OUT</sub> changes from "L" to "H". When the S pole or N pole of a magnet is moved further away from the marking surface of this IC and the magnetic flux density is lower than the release point (B<sub>RPN</sub> or B<sub>RPS</sub>), V<sub>OUT</sub> changes from "H" to "L". **Figure 17** shows the relationship between the magnetic flux density and V<sub>OUT</sub>.

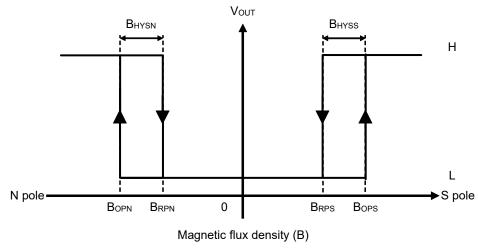


Figure 17

#### 4. Power-on operation

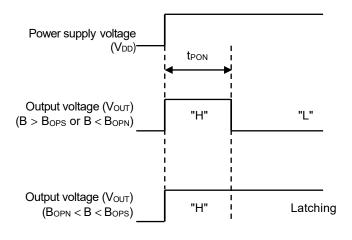
The output voltage ( $V_{OUT}$ ) of this IC immediately after power-on is "H". After the start up time ( $t_{PON}$ ) is passed, the IC changes  $V_{OUT}$  according to the level of the magnetic flux density (N pole or S pole) applied by a magnet.

#### 4.1 Active "L" product

Figure 18 shows the timing chart at power-on for active "L" product.

The initial output voltage at rising of power supply voltage (V<sub>DD</sub>) is "H".

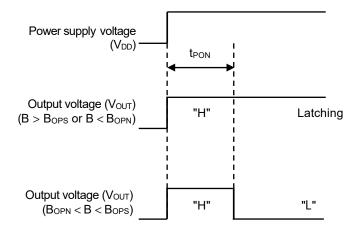
In case of  $B > B_{OPS}$  or  $B < B_{OPN}$  at the time when  $t_{PON}$  is passed after rising of  $V_{DD}$ ,  $V_{OUT}$  changes from "H" to "L". In case of  $B_{OPN} < B < B_{OPS}$  at the time when  $t_{PON}$  is passed after rising of  $V_{DD}$ ,  $V_{OUT}$  retains "H".





#### 4. 2 Active "H" product

**Figure 19** shows the timing chart at power-on for active "H" product. The initial output voltage at rising of power supply voltage (V<sub>DD</sub>) is "H". In case of  $B > B_{OPS}$  or  $B < B_{OPN}$  at the time when t<sub>PON</sub> is passed after rising of V<sub>DD</sub>, V<sub>OUT</sub> retains "H". In case of B<sub>OPN</sub> < B < B<sub>OPS</sub> at the time when t<sub>PON</sub> is passed after rising of V<sub>DD</sub>, V<sub>OUT</sub> changes from "H" to "L".





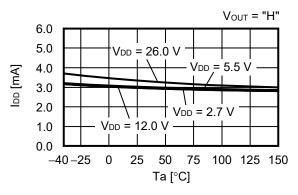
### Precautions

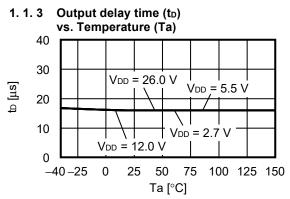
- If the impedance of the power supply is high, the IC may malfunction due to a supply voltage drop caused by feed-through current. Take care with the pattern wiring to ensure that the impedance of the power supply is low.
- Note that the IC may malfunction if the power supply voltage rapidly changes. When the IC is used under the
  environment where the power supply voltage rapidly changes, it is recommended to judge the output voltage of
  the IC by reading it multiple times.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- Note that the output voltage may rarely change if the magnetic flux density between the operation point and the release point is applied to this IC continuously for a long time.
- Although this IC has a built-in output current limit circuit, it may suffer physical damage such as product deterioration under the environment where the absolute maximum ratings are exceeded.
- Although this IC has a built-in reverse voltage protection circuit, it may suffer physical damage such as product deterioration under the environment where the absolute maximum ratings are exceeded.
- The application conditions for the power supply voltage, the pull-up voltage, and the pull-up resistor should not exceed the power dissipation.
- Large stress on this IC may affect the magnetic characteristics. Avoid large stress which is caused by the handling during or after mounting the IC on a board.
- Since the package heat radiation differs according to the conditions of the application, perform thorough evaluation with actual applications to confirm no problems occur.
- ABLIC Inc. claims no responsibility for any disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

# ■ Characteristics (Typical Data)

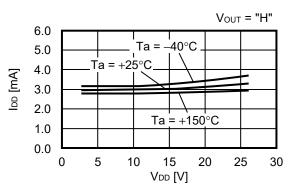
#### 1. Electrical Characteristics

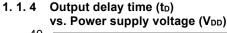
- 1.1 S-57GDxxxS
  - 1. 1. 1 Current consumption (I<sub>DD</sub>) vs. Temperature (Ta)

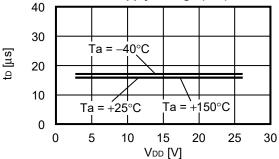




#### 1. 1. 2 Current consumption (IDD) vs. Power supply voltage (VDD)

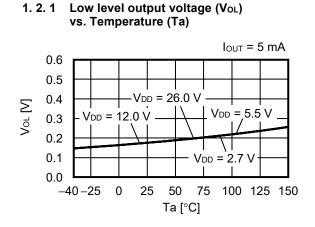




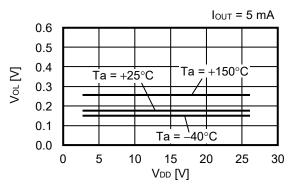


Caution  $V_{DD} = 2.7 \text{ V}$  to 5.5 V when output form is Nch driver + built-in pull-up resistor (1.2 k $\Omega$  typ.). Comply with power supply voltage range and do not exceed absolute maximum ratings.

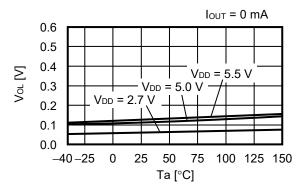
#### 1.2 S-57GDNxxS

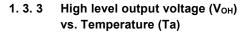


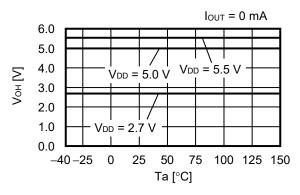
# 1. 2. 2 Low level output voltage (VoL) vs. Power supply voltage (VDD)



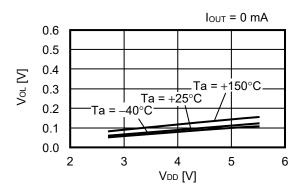
#### 1.3 S-57GD1xxS



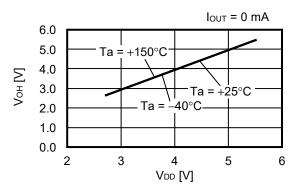




1.3.2 Low level output voltage (V<sub>OL</sub>) vs. Power supply voltage (V<sub>DD</sub>)



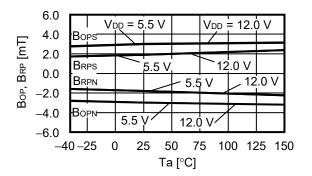
1. 3. 4 High level output voltage (V<sub>OH</sub>) vs. Power supply voltage (V<sub>DD</sub>)



#### 2. Magnetic Characteristics

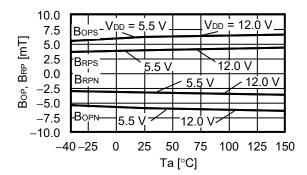
#### 2.1 S-57GDxx1S-L3T2U

2. 1. 1 Operation point, release point (B<sub>OP</sub>, B<sub>RP</sub>) vs. Temperature (Ta)

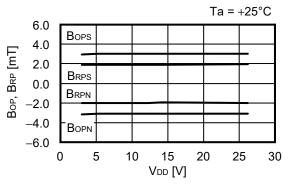


#### 2. 2 S-57GDxx3S-L3T2U

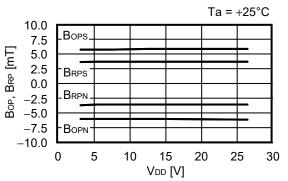
2. 2. 1 Operation point, release point (B<sub>OP</sub>, B<sub>RP</sub>) vs. Temperature (Ta)



2. 1. 2 Operation point, release point (B<sub>OP</sub>, B<sub>RP</sub>) vs. Power supply voltage (V<sub>DD</sub>)



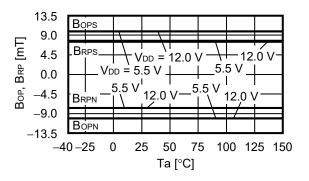
2. 2. 2 Operation point, release point (B<sub>OP</sub>, B<sub>RP</sub>) vs. Power supply voltage (V<sub>DD</sub>)



Caution  $V_{DD} = 2.7$  V to 5.5 V when output form is Nch driver + built-in pull-up resistor (1.2 k $\Omega$  typ.). Comply with power supply voltage range and do not exceed absolute maximum ratings.

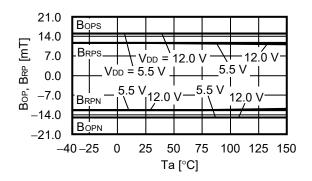
#### 2.3 S-57GDxx4S-L3T2U

2. 3. 1 Operation point, release point (B<sub>OP</sub>, B<sub>RP</sub>) vs. Temperature (Ta)

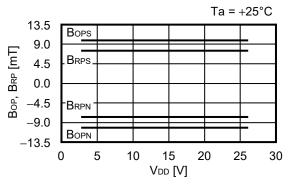


#### 2.4 S-57GDxx5S-L3T2U

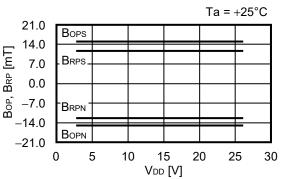
2. 4. 1 Operation point, release point (Bop, BRP) vs. Temperature (Ta)



2. 3. 2 Operation point, release point (B<sub>OP</sub>, B<sub>RP</sub>) vs. Power supply voltage (V<sub>DD</sub>)

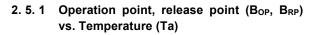


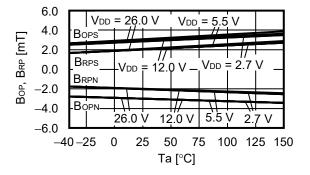
2. 4. 2 Operation point, release point (BoP, BRP) vs. Power supply voltage (V<sub>DD</sub>)



Caution  $V_{DD} = 2.7$  V to 5.5 V when output form is Nch driver + built-in pull-up resistor (1.2 k $\Omega$  typ.). Comply with power supply voltage range and do not exceed absolute maximum ratings.

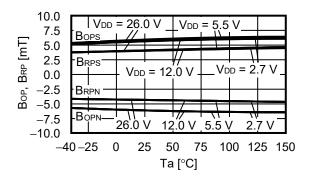
#### 2.5 S-57GDxx1S-A6T8U



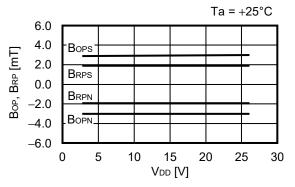


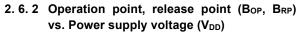
#### 2.6 S-57GDxx3S-A6T8U

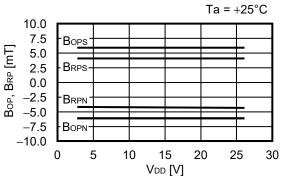
2. 6. 1 Operation point, release point (Bop, BRP) vs. Temperature (Ta)



2. 5. 2 Operation point, release point (B<sub>OP</sub>, B<sub>RP</sub>) vs. Power supply voltage (V<sub>DD</sub>)

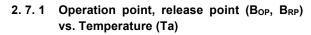


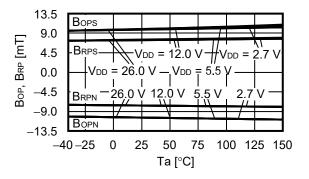




Caution  $V_{DD} = 2.7$  V to 5.5 V when output form is Nch driver + built-in pull-up resistor (1.2 k $\Omega$  typ.). Comply with power supply voltage range and do not exceed absolute maximum ratings.

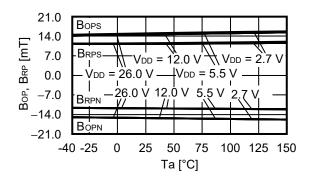
#### 2.7 S-57GDxx4S-A6T8U



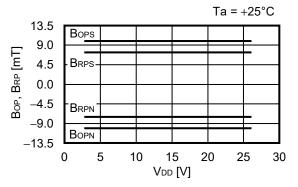


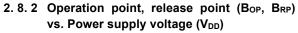
#### 2.8 S-57GDxx5S-A6T8U

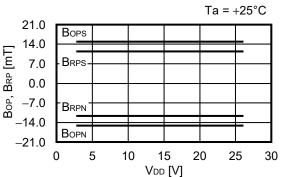
2. 8. 1 Operation point, release point (Bop, BRP) vs. Temperature (Ta)



2. 7. 2 Operation point, release point (B<sub>OP</sub>, B<sub>RP</sub>) vs. Power supply voltage (V<sub>DD</sub>)





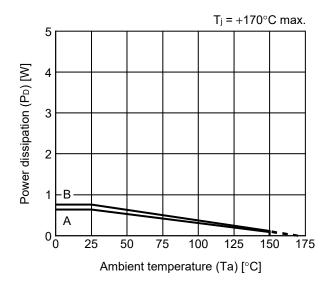


Caution  $V_{DD} = 2.7$  V to 5.5 V when output form is Nch driver + built-in pull-up resistor (1.2 k $\Omega$  typ.). Comply with power supply voltage range and do not exceed absolute maximum ratings.

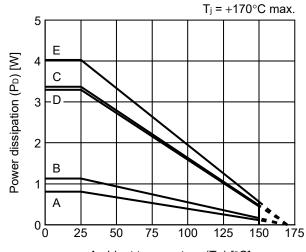
# Power Dissipation

### TSOT-23-3S

### HSNT-6(2025)



Board	Power Dissipation (P <sub>D</sub> )
А	0.64 W
В	0.76 W
С	_
D	_
E	_



Ambient temperature (Ta) [°C]

Board	Power Dissipation (P <sub>D</sub> )
А	0.81 W
В	1.13 W
С	3.37 W
D	3.30 W
E	4.03 W

# TSOT-23-3S Test Board

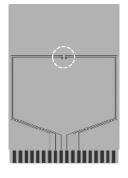
IC Mount Area

# (1) Board A



Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		2
	1	Land pattern and wiring for testing: t0.070
Coppor foil lover [mm]	2	-
Copper foil layer [mm]	3	-
	4	74.2 x 74.2 x t0.070
Thermal via		-

# (2) Board B



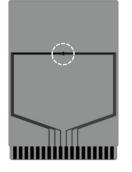
Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
	1	Land pattern and wiring for testing: t0.070
Coppor foil lovor [mm]	2	74.2 x 74.2 x t0.035
Copper foil layer [mm]	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		-

No. TSOT23x-A-Board-SD-1.0

# HSNT-6(2025) Test Board

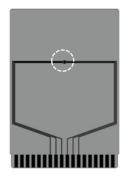
# IC Mount Area

# (1) Board A



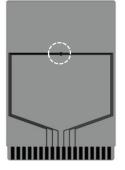
Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		2
	1	Land pattern and wiring for testing: t0.070
Copper foil layer [mm]	2	-
	3	-
	4	74.2 x 74.2 x t0.070
Thermal via		-

(2) Board B



Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		-

# (3) Board C



Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
	1	Land pattern and wiring for testing: t0.070
Copper foil layer [mm]	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		Number: 4 Diameter: 0.3 mm

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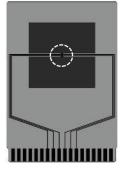
enlarged view

# No. HSNT6-B-Board-SD-1.0

# HSNT-6(2025) Test Board

# ) IC Mount Area

# (4) Board D

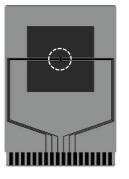


Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
	1	Pattern for heat radiation: 2000mm <sup>2</sup> t0.070
Coppor foil lover [mm]	2	74.2 x 74.2 x t0.035
Copper foil layer [mm]	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		-



enlarged view

#### (5) Board E

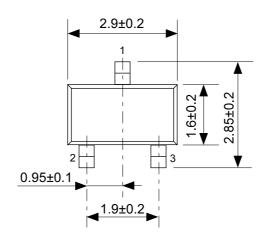


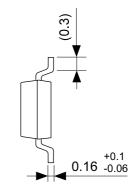
Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
	1	Pattern for heat radiation: 2000mm <sup>2</sup> t0.070
Coppor foil lover [mm]	2	74.2 x 74.2 x t0.035
Copper foil layer [mm]	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		Number: 4 Diameter: 0.3 mm

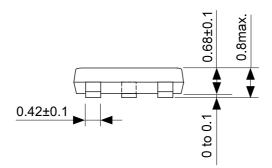


enlarged view

No. HSNT6-B-Board-SD-1.0

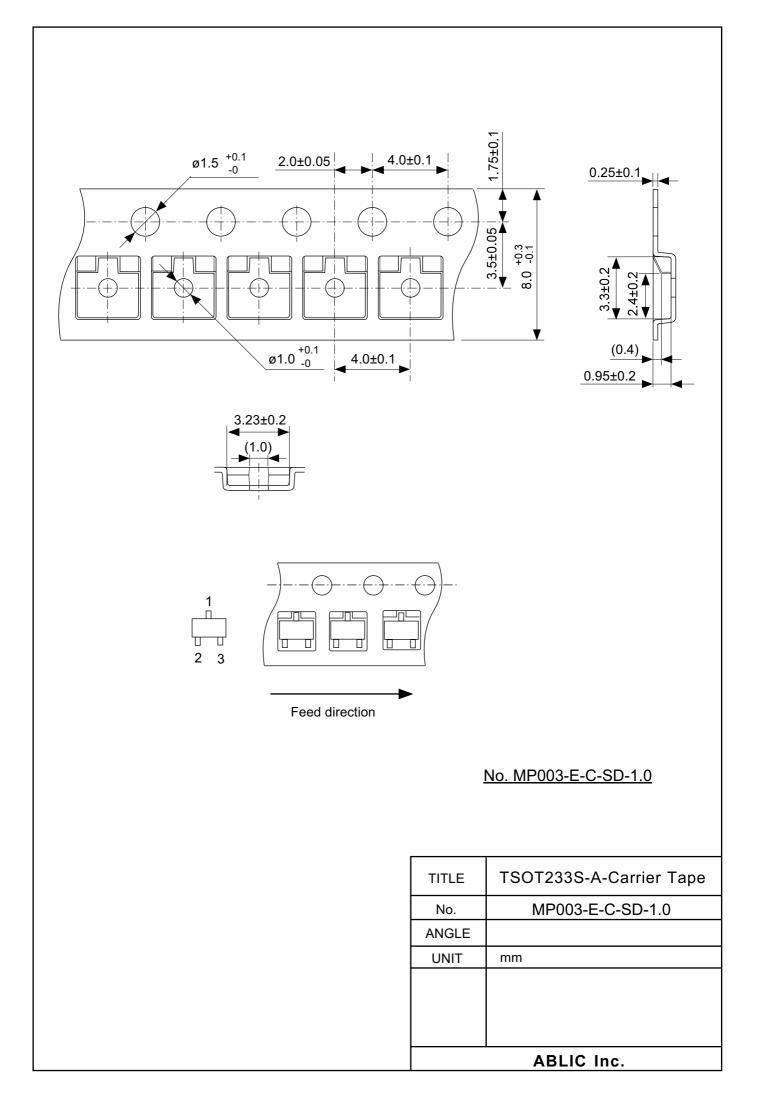


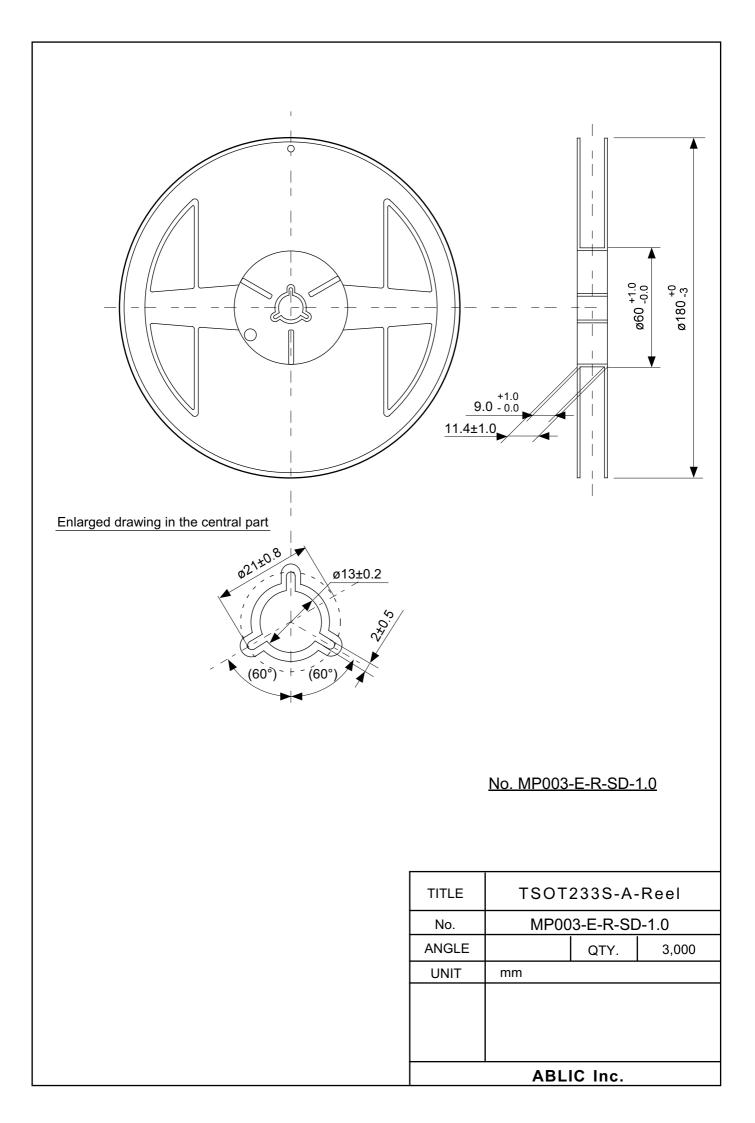


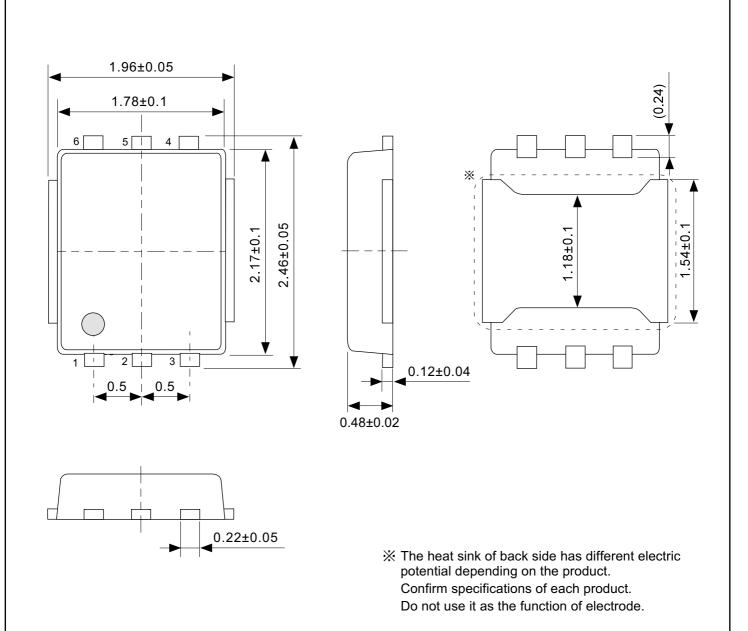


No. MP003-E-P-SD-1.0

TITLE	TSOT233S-A-PKG Dimensions			
No.	MP003-E-P-SD-1.0			
ANGLE	$\Phi$			
UNIT	mm			
ABLIC Inc.				

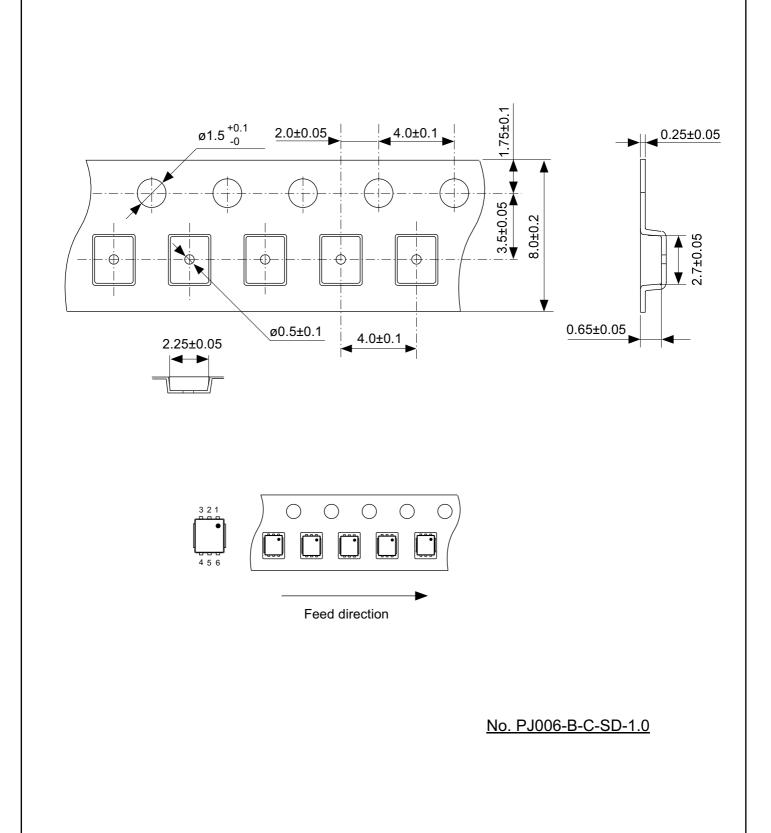




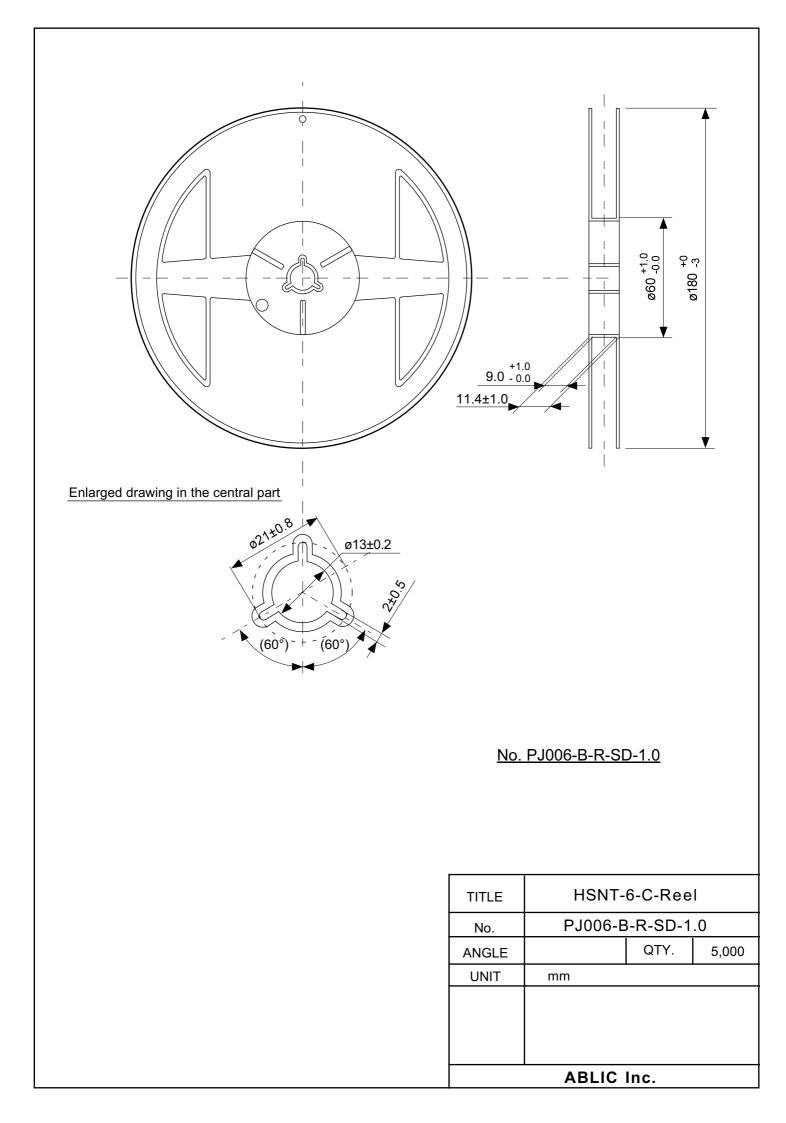


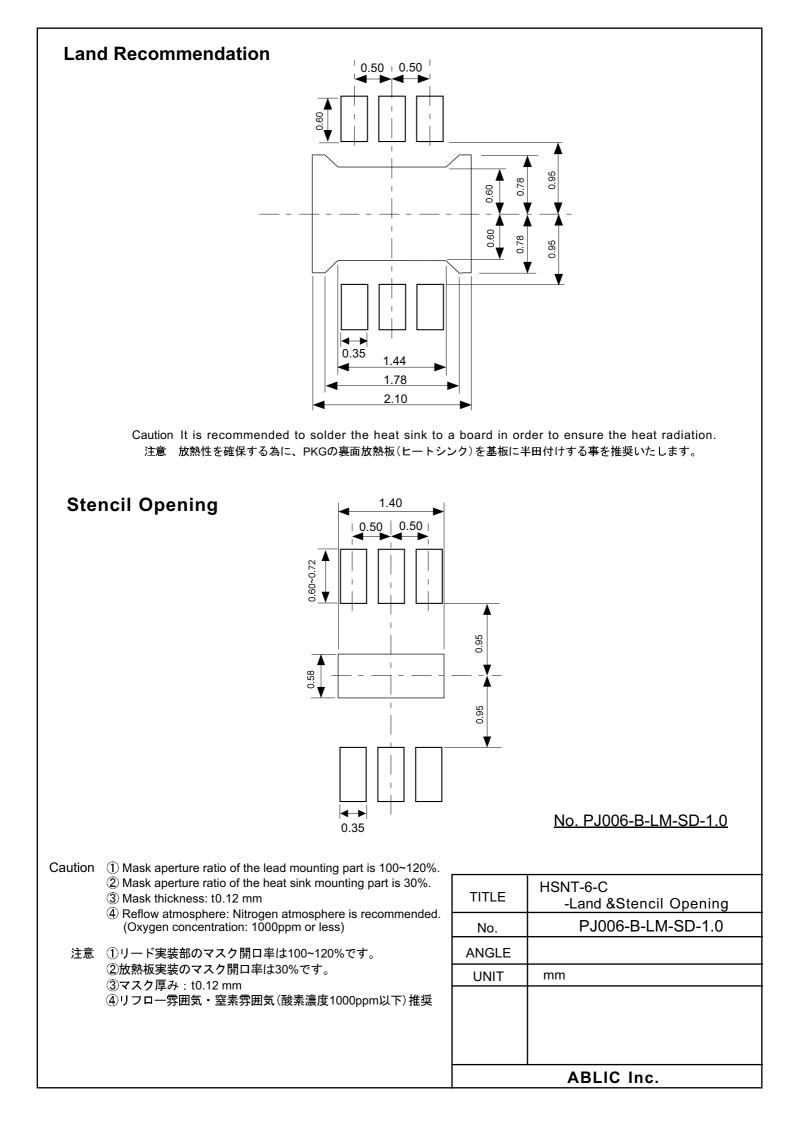
#### No. PJ006-B-P-SD-1.0

TITLE	HSNT-6-C-PKG Dimensions			
No.	PJ006-B-P-SD-1.0			
ANGLE	$\bigoplus \Box$			
UNIT	mm			
ABLIC Inc.				



TITLE	HSNT-6-C-Carrier Tape
No.	PJ006-B-C-SD-1.0
ANGLE	
UNIT	mm
ABLIC Inc.	





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2.4-2019.07